6-BIT, 1-of-2 MULTIPLEXER/DEMULTIPLEXER WITH INTEGRATED IEC L-4 ESD AND 1.8-V LOGIC COMPATIBLE CONTROL INPUTS

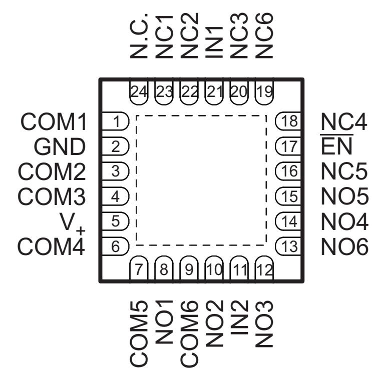
FEATURES

- **1.65-V to 3.6-V Single-Supply Operation**
- **Isolation in Powerdown Mode, $V_+ = 0$**
- **Low Capacitance Switches, 21.5 pF (Typical)**
- **Bandwidth up to 240 MHz for High-Speed Rail-to-Rail Signal Handling**
- **Crosstalk and Off Isolation of -62dB**
- **1.8-V Logic Threshold Compatibility for Control Inputs**
- **3.6-V Tolerant Control Inputs**
- **Latch-Up Performance Exceeds 100-mA Per JESD 78, Class II**
- **ESD Performance Tested Per JESD 22**
  - **2500-V Human-Body Model (A114-B, Class II)**
  - **1500-V Charged-Device Model (C101)**
- **ESD Performance: NC/NO Ports**
  - **±6-kV Contact Discharge (IEC 61000-4-2)**
- **24-QFN (4 × 4 mm), 24-BGA (3 × 3 mm) and 24-TSSOP (7.9 × 6.6 mm) Packages**

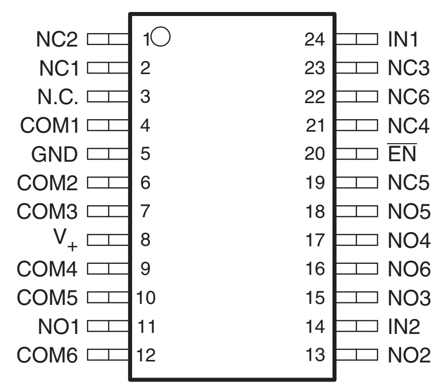
APPLICATIONS

- **SD/SDIO and MMC Two Port MUX**
- **PC VGA Video MUX/Video Systems**
- **Audio and Video Signal Routing**

RTW PACKAGE (TOP VIEW)

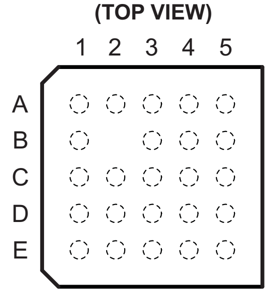


PW PACKAGE (TOP VIEW)



N.C. – Not internally connected

ZQS PACKAGE (TOP VIEW)



ZQS PIN ASSIGNMENTS

	1	2	3	4	5
A	COM1	NC2	N.C.	NC3	NC6
B	COM2		NC1	IN1	NC4
C	COM3	V_+	GND	$\overline{EN}$	NC5
D	COM4	COM6	IN2	NO5	NO4
E	COM5	NO1	NO2	NO3	NO6

DESCRIPTION/ORDERING INFORMATION

The TS3A27518E is a 6-bit 1-of-2 Mux/Demux designed to operate from 1.65 V to 3.6 V. This device can handle both digital and analog signals, and signals up to V_+ can be transmitted in either direction. The TS3A27518E has two control pins, each controlling three 1-of-2 muxes at the same time, and an enable pin that is used to put all outputs in high-impedance mode. The control pins are compatible with 1.8V logic thresholds and are backward compatible with 2.5 V and 3.3 V logic thresholds as well.

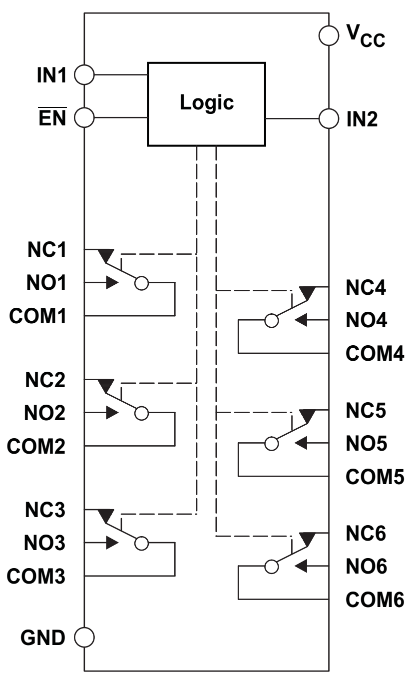
The TS3A27518E allows any SD, SDIO, and multimedia card host controllers to be expanded out to multiple cards or peripherals since the SDIO interface consists of 6-bits: CMD, CLK, and Data[0:3] signals. The TS3A27518E has two control pins that give additional flexibility to the user. For example, the ability to mux two different audio-video signals in equipment such as an LCD television,an LCD monitor, or a notebook docking station.

ORDERING INFORMATION

T_A	PACKAGE(1)(2)		ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 85°C	BGA – ZQS	Tape and reel	TS3A27518EZQSR	YL518E
	QFN – RTW	Tape and reel	TS3A27518ERTWR	YL518E
	TSSOP – PW	Tape and reel	TS3A27518EPWR	YL518E

(1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.
(2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

LOGIC DIAGRAM



SUMMARY OF CHARACTERISTICS

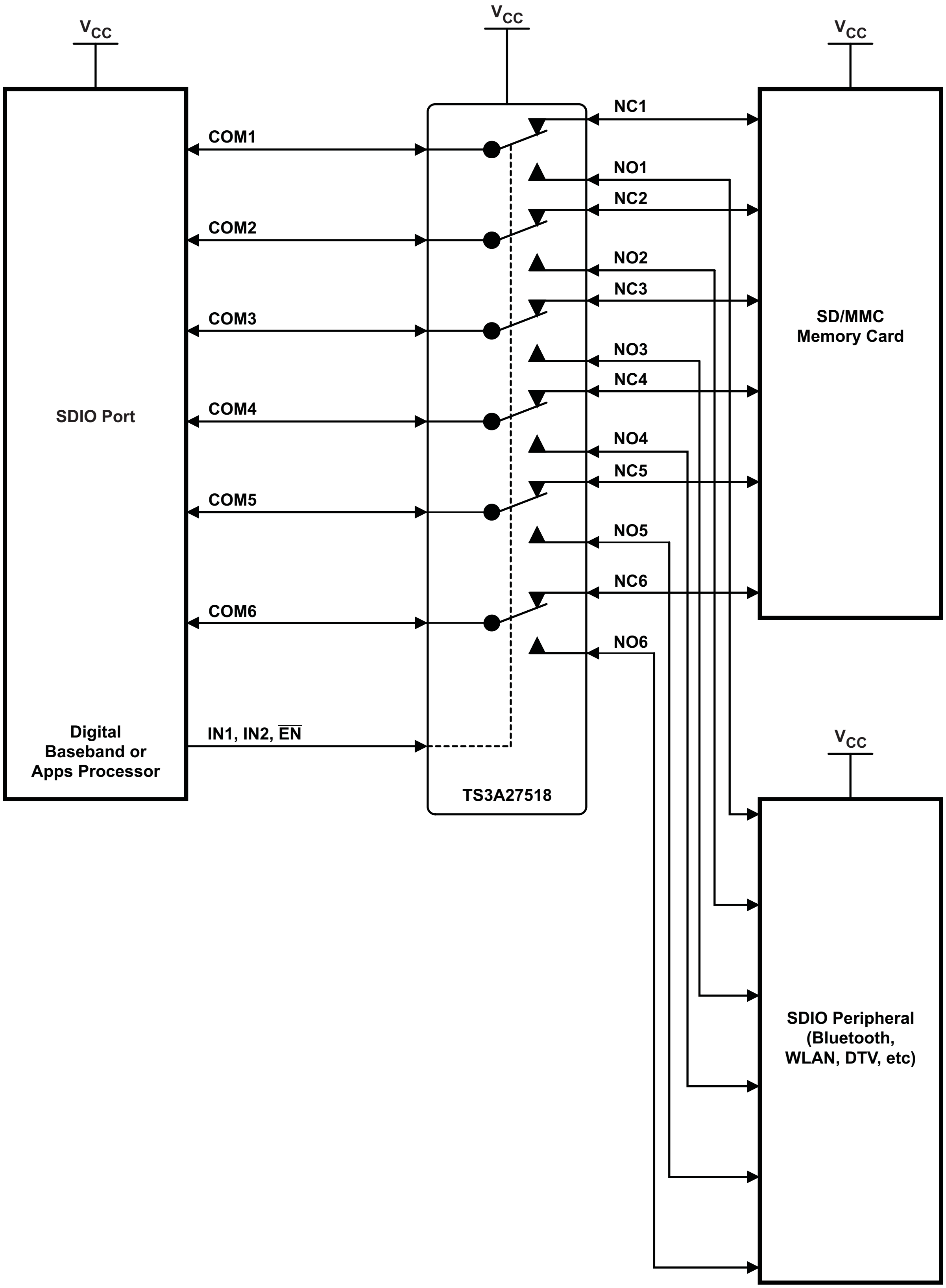
$V_+ = 3.3$ V, $T_A = 25°C$

Configuration	1-of-2 Multiplexer/Demultiplexer
Number of channels	6
ON-state resistance (r_{on})	6.2 Ω (max)
ON-state resistance match (Δr_{on})	0.7 Ω (max)
ON-state resistance flatness ($r_{ON(flat)}$)	2.1 Ω (max)
Turn-on/turn-off time (t_{ON}/t_{OFF})	59 ns/ 60.6 ns (max)
Break-before-make time (t_{BBM})	22.7 ns (max)
Charge injection (Q_C)	0.81 pC
Bandwidth (BW)	240 MHz
OFF isolation (O_{ISO})	–62 dB at 10 MHz
Crosstalk (X_{TALK})	–62 dB at 10 MHz
Total harmonic distortion (THD)	0.05%
Power-supply current (I_+)	< 0.3 µA (max)
Package options	24-pin QFN (RTW), 24-BGA (ZQS) 24-TSSOP (PW)

FUNCTION TABLE

$\overline{EN}$	IN1	IN2	NC1/2/3 TO COM1/2/3, COM1/2/3 TO NC1/2/3	NC4/5/6 TO COM4/5/6, COM4/5/6 TO NC4/5/6	NO1/2/3 TO COM1/2/3, COM1/2/3 TO NO1/2/3	NO4/5/6 TO COM4/5/6, COM4/5/6 TO NO4/5/6
H	X	X	OFF	OFF	OFF	OFF
L	L	L	ON	ON	OFF	OFF
L	H	L	OFF	ON	ON	OFF
L	L	H	ON	OFF	OFF	ON
L	H	H	OFF	OFF	ON	ON

SDIO EXPANDER APPLICATION BLOCK DIAGRAM



ABSOLUTE MINIMUM AND MAXIMUM RATINGS(1)(2)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_+	Supply voltage range(3)		–0.5	4.6	V
V_{NC} V_{NO} V_{COM}	Analog voltage range(3)(4)(5)		–0.5	4.6	V
I_K	Analog port diode current(6)	$V_+ < V_{NC}, V_{NO}, V_{COM} < 0$	–50		mA
I_{NC} I_{NO} I_{COM}	ON-state switch current(7)	V_{NC}, V_{NO}, V_{COM} = 0 to V_+	–50	50	mA
V_I	Digital input voltage range(3)(4)		–0.5	4.6	V
I_{IK}	Digital input clamp current(3)(4)	$V_{IO} < V_I < 0$	–50		mA
I_+	Continuous current through V_+			100	mA
I_{GND}	Continuous current through GND		–100		mA
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
(2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
(3) All voltages are with respect to ground, unless otherwise specified.
(4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(5) This value is limited to 5.5 V maximum.
(6) Requires clamp diodes on analog port to V_+.
(7) Pulse at 1-ms duration <10% duty cycle

THERMAL IMPEDANCE RATINGS

				UNIT
θ_{JA}	Package thermal impedance(1)	PW package	87.9	°C/W
		RTW package	66	
		ZQS package	171.6	

(1) The package thermal impedance is calculated in accordance with JESD 51-7.

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY(1)

V_+ = 3 V to 3.6 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V_+	Ω
ON-state resistance	r_{on}	$0 \le (V_{NC}$ or $V_{NO}) \le V_+$, I_{COM} = –32 mA,	Switch ON, See Figure 15	25°C	3 V		4.4	6.2	Ω
				Full				7.6	
ON-state resistance match between channels	Δr_{on}	V_{NC} or V_{NO} = 2.1 V, I_{COM} = –32 mA,	Switch ON, See Figure 15	25°C	3 V		0.3	0.7	Ω
				Full				0.8	
ON-state resistance flatness	$r_{on(flat)}$	$0 \le (V_{NC}$ or $V_{NO}) \le V_+$, I_{COM} = –32 mA,	Switch ON, See Figure 16	25°C	3 V		0.95	2.1	Ω
				Full				2.3	
NC, NO OFF leakage current	$I_{NC(OFF)}$, $I_{NO(OFF)}$	V_{NC} or V_{NO} = 1 V, V_{COM} = 3 V, or V_{NC} or V_{NO} = 3 V, V_{COM} = 1 V,	Switch OFF, See Figure 16	25°C	3.6 V	–0.5	0.05	0.5	μA
				Full		–7		7	
	$I_{NC(PWROFF)}$, $I_{NO(PWROFF)}$	V_{NC} or V_{NO} = 0 to 3.6 V, V_{COM} = 3.6 V to 0, or V_{NC} or V_{NO} = 3.6 V to 0, V_{COM} = 0 to 3.6 V,		25°C	0 V	–1	0.05	1	
				Full		–12		12	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY (continued)

V_+ = 3 V to 3.6 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
COM OFF leakage current	$I_{COM(OFF)}$	V_{NC} or V_{NO} = 3 V, V_{COM} = 1 V, or V_{NC} or V_{NO} = 1 V, V_{COM} = 3 V,	Switch OFF, See Figure 16	25°C	3.6 V	–1	0.01	1	µA
				Full		–2		2	
	$I_{COM(PWROFF)}$	V_{NC} or V_{NO} = 3.6 V to 0, V_{COM} = 0 to 3.6 V, or V_{NC} or V_{NO} = 0 to 3.6 V, V_{COM} = 3.6 V to 0,		25°C	0 V	–1	0.02	1	
				Full		–12		1	
NC, NO ON leakage current	$I_{NO(ON)}$, $I_{NC(ON)}$	V_{NC} or V_{NO} = 1 V, V_{COM} = Open, or V_{NC} or V_{NO} = 3 V, V_{COM} = Open,	Switch ON, See Figure 17	25°C	3.6 V	–2.5	0.04	2.2	µA
				Full		–7		7	
COM ON leakage current	$I_{COM(ON)}$	V_{NC} or V_{NO} = Open, V_{COM} = 1 V, or V_{NC} or V_{NO} = Open, V_{COM} = 3 V,	Switch ON, See Figure 17	25°C	3.6 V	–2	0.03	2	µA
				Full		–7		7	
Digital Control Inputs (IN1, IN2, $\overline{EN}$)(2)									
Input logic high	V_{IH}			Full	3.6 V	1.2		3.6	V
Input logic low	V_{IL}			Full	3.6 V	0		0.65	V
Input leakage current	I_{IH}, I_{IL}	$V_I = V_+$ or 0		25°C	3.6 V	–0.1	0.05	0.1	µA
				Full		–2.5		2.5	
Dynamic									
Turn-on time	t_{ON}	$V_{COM} = V_+$, R_L = 50 Ω,	C_L = 35 pF, See Figure 19	25°C	3.3 V		18.1	59	ns
				Full	3 V to 3.6 V			60	
Turn-off time	t_{OFF}	$V_{COM} = V_+$, R_L = 50 Ω,	C_L = 35 pF, See Figure 19	25°C	3.3 V		25.4	60.6	ns
				Full	3 V to 3.6 V			61	
Break-before-make time	t_{BBM}	$V_{NC} = V_{NO} = V_+/2$, R_L = 50 Ω,	C_L = 35 pF, See Figure 20	25°C	3.3 V	4	11.1	22.7	ns
				Full	3 V to 3.6 V			28	
Charge injection	Q_C	V_{GEN} = 0, R_{GEN} = 0,	C_L = 0.1 nF, See Figure 24	25°C	3.3 V		0.81		pC
NC, NO OFF capacitance	$C_{NC(OFF)}$, $C_{NO(OFF)}$	V_{NC} or V_{NO} = V_+ or GND, Switch OFF,	See Figure 18	25°C	3.3 V		13		pF
COM OFF capacitance	$C_{COM(OFF)}$	V_{NC} or V_{NO} = V_+ or GND, Switch OFF,	See Figure 18		3.3 V		8.5		pF
NC, NO ON capacitance	$C_{NC(ON)}$, $C_{NO(ON)}$	V_{NC} or V_{NO} = V_+ or GND, Switch OFF,	See Figure 18	25°C	3.3 V		21.5		pF
COM ON capacitance	$C_{COM(ON)}$	V_{COM} = V_+ or GND, Switch ON,	See Figure 18	25°C	3.3 V		21.5		pF
Digital input capacitance	C_I	$V_I = V_+$ or GND	See Figure 18	25°C	3.3 V		2		pF
Bandwidth	BW	R_L = 50 Ω,	Switch ON, See Figure 20	25°C	3.3 V		240		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 10 MHz,	Switch OFF, See Figure 22	25°C	3.3 V		–62		dB
Crosstalk	X_{TALK}	R_L = 50 Ω, f = 10 MHz,	Switch ON, See Figure 23	25°C	3.3 V		–62		dB
Crosstalk adjacent	$X_{TALK(ADJ)}$	R_L = 50 Ω, f = 10 MHz,	Switch ON, See Figure 23	25°C	3.3 V		–71		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 25	25°C	3.3 V		0.05		%
Supply									
Positive supply current	I_+	$V_I = V_+$ or GND,	Switch ON or OFF	25°C	3.6 V		0.04	0.3	µA
				Full				3	

(2) All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY(1)

V_+ = 2.3 V to 2.7 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V_+	Ω
ON-state resistance	r_{on}	0 ≤ (V_{NC} or V_{NO}) ≤ V_+, I_{COM} = –32 mA,	Switch ON, See Figure 15	25°C	2.3 V		5.5	9.6	Ω
				Full				11.5	
ON-state resistance match between channels	Δr_{on}	V_{NC} or V_{NO} = 1.6 V, I_{COM} = –32 mA,	Switch ON, See Figure 15	25°C	2.3 V		0.3	0.8	Ω
				Full				0.9	
ON-state resistance flatness	$r_{on(flat)}$	0 ≤ (V_{NC} or V_{NO}) ≤ V_+, I_{COM} = –32 mA,	Switch ON, See Figure 16	25°C	2.3 V		0.91	2.2	Ω
				Full				2.3	
NC, NO OFF leakage current	$I_{NC(OFF)}$, $I_{NO(OFF)}$	V_{NC} or V_{NO} = 0.5 V, V_{COM} = 2.3 V, or V_{NC} or V_{NO} = 2.3 V, V_{COM} = 0.5 V,	Switch OFF, See Figure 16	25°C	2.7 V	–0.3	0.04	0.3	µA
				Full		–6		6	
	$I_{NC(PWROFF)}$, $I_{NO(PWROFF)}$	V_{NC} or V_{NO} = 0 to 2.7 V, V_{COM} =2.7 V to 0, or V_{NC} or V_{NO} = 2.7 V to 0, V_{COM} = 0 to 2.7 V,		25°C	0 V	–0.6	0.02	0.6	
				Full		–10		10	
COM OFF leakage current	$I_{COM(OFF)}$	V_{NC} or V_{NO} = 0.5 V, V_{COM} = 2.3 V, or V_{NC} or V_{NO} = 2.3 V, V_{COM} = 0.5 V,	Switch OFF, See Figure 16	25°C	2.7 V	–0.7	0.02	0.7	µA
				Full		–1		1	
	$I_{COM(PWROFF)}$	V_{NC} or V_{NO} = 2.7 V to 0, V_{COM} = 0 to 2.7 V, or V_{NC} or V_{NO} = 0 to 2.7 V, V_{COM} = 2.7 V to 0,		25°C	0 V	–0.7	0.02	0.7	
				Full		–7.2		7.2	
NC, NO ON leakage current	$I_{NO(ON)}$, $I_{NC(ON)}$	V_{NC} or V_{NO} = 0.5 V or 2.3 V, V_{COM} = Open,	Switch ON, See Figure 17	25°C	2.7 V	–2.1	0.03	2.1	µA
				Full		–6		6	
COM ON leakage current	$I_{COM(ON)}$	V_{NC} or V_{NO} = Open, V_{COM} = 0.5 V, or V_{NC} or V_{NO} = Open, V_{COM} = 2.3 V,	Switch ON, See Figure 17	25°C	2.7 V	–2	0.02	2	µA
				Full		–5.7		5.7	
Digital Control Inputs (IN1, IN2, $\overline{EN}$)(2)									
Input logic high	V_{IH}	V_I = V_+ or GND		Full	2.7 V	1.15		3.6	V
Input logic low	V_{IL}			Full	2.7 V	0		0.55	V
Input leakage current	I_{IH}, I_{IL}	V_I = V_+ or 0		25°C	2.7 V	-0.1	0.01	0.1	µA
				Full		–2.1		2.1	
Dynamic									
Turn-on time	t_{ON}	V_{COM} = V+, R_L = 50 Ω,	C_L = 35 pF, See Figure 19	25°C	2.5 V		17.2	36.8	ns
				Full	2.3 V to 2.7 V			42.5	
Turn-off time	t_{OFF}	V_{COM} = V+, R_L = 50 Ω,	C_L = 35 pF, See Figure 19	25°C	2.5 V		17.1	29.8	ns
				Full	2.3 V to 2.7 V			34.4	
Break-before-make time	t_{BBM}	V_{NC} = V_{NO} = V_+/2, R_L = 50 Ω,	C_L = 35 pF, See Figure 20	25°C	2.5 V	4.5	13	30	ns
				Full	2.3 V to 2.7 V			33.3	
Charge injection	Q_C	V_{GEN} = 0, R_{GEN} = 0,	C_L = 0.1 nF, See Figure 24	25°C	2.5 V		0.47		pC
NC, NO OFF capacitance	$C_{NC(OFF)}$, $C_{NO(OFF)}$	V_{NC} or V_{NO} = V_+ or GND, Switch OFF,	See Figure 18	25°C	2.5 V		13.5		pF
COM OFF capacitance	$C_{COM(OFF)}$	V_{NC} or V_{NO} = V_+ or GND, Switch OFF,	See Figure 18		2.5 V		9		pF

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
(2) All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY (continued)

V_+ = 2.3 V to 2.7 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
NC, NO ON capacitance	$C_{NC(ON)}$, $C_{NO(ON)}$	V_{NC} or V_{NO} = V_+ or GND, Switch OFF,	See Figure 18	25°C	2.5 V		22		pF
COM ON capacitance	$C_{COM(ON)}$	V_{COM} = V_+ or GND, Switch ON,	See Figure 18	25°C	2.5 V		22		pF
Digital input capacitance	C_I	V_I = V_+ or GND	See Figure 18	25°C	2.5 V		2		pF
Bandwidth	BW	R_L = 50 Ω,	Switch ON, See Figure 20	25°C	2.5 V		240		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 10 MHz,	Switch OFF, See Figure 22	25°C	2.5 V		–62		dB
Crosstalk	X_{TALK}	R_L = 50 Ω, f = 10 MHz,	Switch ON, See Figure 23	25°C	2.5 V		–62		dB
Crosstalk adjacent	$X_{TALK(ADJ)}$	R_L = 50 Ω, f = 10 MHz,	Switch ON, See Figure 23	25°C	2.5 V		–71		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 25	25°C	2.5 V		0.06		%
Supply									
Positive supply current	I_+	V_I = V_+ or GND,	Switch ON or OFF	25°C	2.7 V		0.01	0.1	μA
				Full				2	

ELECTRICAL CHARACTERISTICS FOR 1.8-V SUPPLY(1)

V_+ = 1.65 V to 1.95 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V_+	Ω
ON-state resistance	r_{on}	0 ≤ (V_{NC} or V_{NO}) ≤ V_+, I_{COM} = –32 mA,	Switch ON, See Figure 15	25°C	1.65 V		7.1	14.4	Ω
				Full				16.3	
ON-state resistance match between channels	Δr_{on}	V_{NC} or V_{NO} = 1.5 V, I_{COM} = –32 mA,	Switch ON, See Figure 15	25°C	1.65 V		0.3	1	Ω
				Full				1.2	
ON-state resistance flatness	$r_{on(flat)}$	0 ≤ (V_{NC} or V_{NO}) ≤ V_+, I_{COM} = –32 mA,	Switch ON, See Figure 16	25°C	1.65 V		2.7	5.5	Ω
				Full				7.3	
NC, NO OFF leakage current	$I_{NC(OFF)}$, $I_{NO(OFF)}$	V_{NC} or V_{NO} = 0.3 V, V_{COM} = 1.65 V, or V_{NC} or V_{NO} = 1.65 V, V_{COM} = 0.3 V	Switch OFF, See Figure 16	25°C	1.95 V	–0.25	0.03	0.25	μA
				Full		–5		5	
	$I_{NC(PWROFF)}$, $I_{NO(PWROFF)}$	V_{NC} or V_{NO} = 1.95 V to 0, V_{COM} = 0 to 1.95 V, or V_{NC} or V_{NO} = 0 to 1.95 V, V_{COM} = 1.95 V to 0,		25°C	0 V	–0.4	0.01	0.4	μA
				Full		–7.2		7.2	
COM OFF leakage current	$I_{COM(OFF)}$, $I_{COM(OFF)}$	V_{NC} or V_{NO} = 0.3 V, V_{COM} = 1.65 V, or V_{NC} or V_{NO} = 1.65 V, V_{COM} = 0.3 V	Switch OFF, See Figure 16	25°C	1.95 V	–0.4	0.02	0.4	μA
				Full		–0.9		0.9	
	$I_{COM(PWROFF)}$, $I_{COM(PWROFF)}$	V_{NC} or V_{NO} = 1.95 V to 0, V_{COM} = 0 to 1.95 V, or V_{NC} or V_{NO} = 0 to 1.95 V, V_{COM} = 1.95 V to 0,		25°C	0 V	–0.4	0.02	0.4	μA
				Full		–5		5	
NC, NO ON leakage current	$I_{NO(ON)}$, $I_{NC(ON)}$	V_{NC} or V_{NO} = 0.3 V, V_{COM} = Open, or V_{NC} or V_{NO} = 1.65 V, V_{COM} = Open,	Switch ON, See Figure 17	25°C	1.95 V	–2	0.02	2	μA
				Full		–5.2		5.2	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

ELECTRICAL CHARACTERISTICS FOR 1.8-V SUPPLY (continued)

V_+ = 1.65 V to 1.95 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
COM ON leakage current	$I_{COM(ON)}$	V_{NC} or V_{NO} = Open, V_{COM} = 0.3 V, or V_{NC} or V_{NO} = Open, V_{COM} = 1.65 V,	Switch ON, See Figure 17	25°C	1.95 V	–2	0.02	2	µA
				Full		–5.2		5.2	
Digital Control Inputs (IN1, IN2, $\overline{EN}$) (2)									
Input logic high	V_{IH}	$V_I = V_+$ or GND		Full	1.95 V	1		3.6	V
Input logic low	V_{IL}			Full	1.95 V	0		0.4	V
Input leakage current	I_{IH}, I_{IL}	$V_I = V_+$ or 0		25°C	1.95 V	-0.1	0.01	0.1	µA
				Full		-2.1		2.1	
Dynamic									
Turn-on time	t_{ON}	$V_{COM} = V_+$, R_L = 50 Ω,	C_L = 35 pF, See Figure 19	25°C	1.8 V		14.1	49.3	ns
				Full	1.65 V to 1.95 V			56.7	
Turn-off time	t_{OFF}	$V_{COM} = V_+$, R_L = 50 Ω,	C_L = 35 pF, See Figure 19	25°C	1.8 V		16.1	26.5	ns
				Full	1.65 V to 1.95 V			31.2	
Break-before-make time	t_{BBM}	$V_{NC} = V_{NO} = V_+/2$, R_L = 50 Ω,	C_L = 35 pF, See Figure 20	25°C	1.8 V	5.3	18.4	58	ns
				Full	1.65 V to 1.95 V			58	
Charge injection	Q_C	V_{GEN} = 0, R_{GEN} = 0,	C_L = 1 nF, See Figure 24	25°C	1.8 V		0.21		pC
NC, NO OFF capacitance	$C_{NC(OFF)}$, $C_{NO(OFF)}$	V_{NC} or V_{NO} = V_+ or GND, Switch OFF,	See Figure 18	25°C	1.8 V		9		pF
NC, NO ON capacitance	$C_{NC(ON)}$, $C_{NO(ON)}$	V_{NC} or V_{NO} = V_+ or GND, Switch OFF,	See Figure 18	25°C	1.8 V		22		pF
COM ON capacitance	$C_{COM(ON)}$	V_{COM} = V_+ or GND, Switch ON,	See Figure 18	25°C	1.8 V		22		pF
Digital input capacitance	C_I	$V_I = V_+$ or GND	See Figure 18	25°C	1.8 V		2		pF
Bandwidth	BW	R_L = 50 Ω,	Switch ON, See Figure 20	25°C	1.8 V		240		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 10 MHz,	Switch OFF, See Figure 22	25°C	1.8 V		-60		dB
Crosstalk	X_{TALK}	R_L = 50 Ω, f = 10 MHz,	Switch ON, See Figure 23	25°C	1.8 V		-60		dB
Crosstalk adjacent	$X_{TALK(ADJ)}$	R_L = 50 Ω, f = 10 MHz,	Switch ON, See Figure 23	25°C	1.8 V		-71		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 25	25°C	1.8 V		0.1		%
Supply									
Positive supply current	I_+	$V_I = V_+$ or GND,	Switch ON or OFF	25°C	1.95 V		0.01	0.1	µA
				Full				1.5	

(2) All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

PARAMETER DESCRIPTION

SYMBOL	DESCRIPTION
V_{COM}	Voltage at COM
V_{NC}	Voltage at NC
V_{NO}	Voltage at NO
r_{on}	Resistance between COM and NC or NO ports when the channel is ON
Δr_{on}	Difference of r_{on} between channels in a specific device
$r_{on(flat)}$	Difference between the maximum and minimum value of r_{on} in a channel over the specified range of conditions
$I_{NC(OFF)}$	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state
$I_{NC(ON)}$	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) open
$I_{NO(OFF)}$	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state
$I_{NO(ON)}$	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) open
$I_{COM(OFF)}$	Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the OFF state
$I_{COM(ON)}$	Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the ON state and the output (NC or NO) open
V_{IH}	Minimum input voltage for logic high for the control input (IN, $\overline{EN}$)
V_{IL}	Maximum input voltage for logic low for the control input (IN, $\overline{EN}$)
V_I	Voltage at the control input (IN, $\overline{EN}$)
I_{IH}, I_{IL}	Leakage current measured at the control input (IN, $\overline{EN}$)
t_{ON}	Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output NC or NO) signal when the switch is turning ON.
t_{OFF}	Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (NC or NO) signal when the switch is turning OFF.
Q_C	Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC or NO) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, $Q_C = C_L \times \Delta V_{COM}$, C_L is the load capacitance and ΔV_{COM} is the change in analog output voltage.
$C_{NC(OFF)}$	Capacitance at the NC port when the corresponding channel (NC to COM) is OFF
$C_{NC(ON)}$	Capacitance at the NC port when the corresponding channel (NC to COM) is ON
$C_{NO(OFF)}$	Capacitance at the NC port when the corresponding channel (NO to COM) is OFF
$C_{NO(ON)}$	Capacitance at the NC port when the corresponding channel (NO to COM) is ON
$C_{COM(OFF)}$	Capacitance at the COM port when the corresponding channel (COM to NC) is OFF
$C_{COM(ON)}$	Capacitance at the COM port when the corresponding channel (COM to NC) is ON
C_I	Capacitance of control input (IN, $\overline{EN}$)
O_{ISO}	OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM) in the OFF state.
X_{TALK}	Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC1 to NO1). Adjacent crosstalk is a measure of unwanted signal coupling from an ON channel to an adjacent ON channel (NC1 to NC2) .This is measured in a specific frequency and in dB.
BW	Bandwidth of the switch. This is the frequency in which the gain of an ON channel is –3 dB below the DC gain.
THD	Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.
I_+	Static power-supply current with the control (IN) pin at V_+ or GND

TYPICAL CHARACTERISTICS

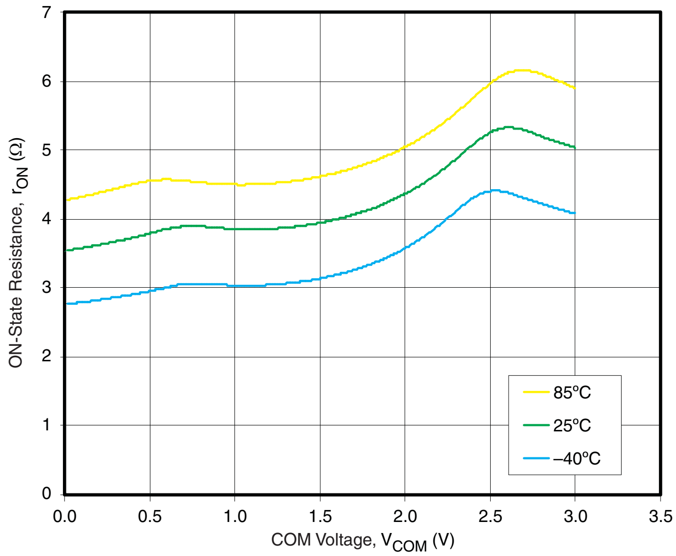


Figure 1. ON-State Resistance vs COM Voltage (V_+ = 3 V)

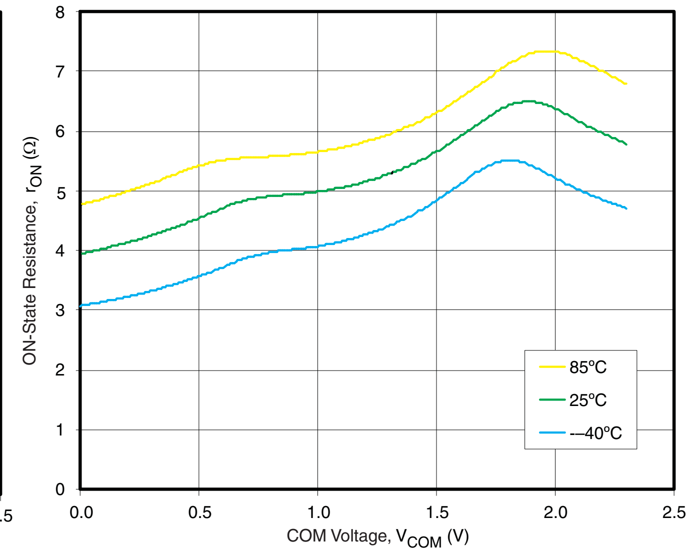


Figure 2. ON-State Resistance vs COM Voltage (V_+ = 2.3 V)

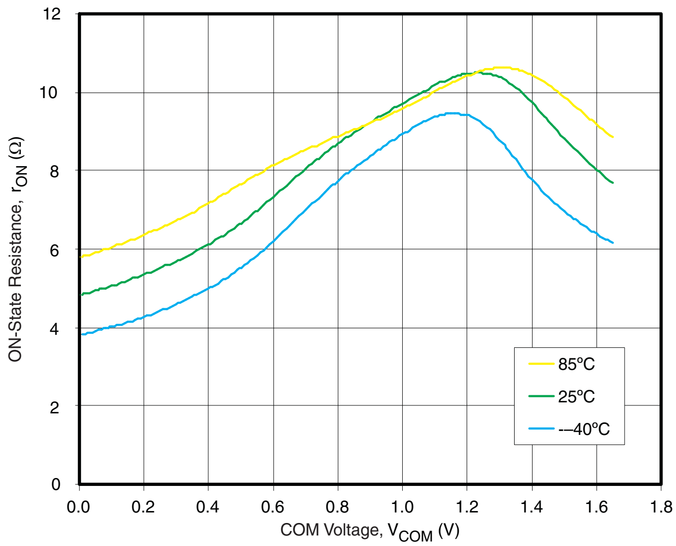


Figure 3. ON-State Resistance vs COM Voltage (V_+ = 1.65 V)

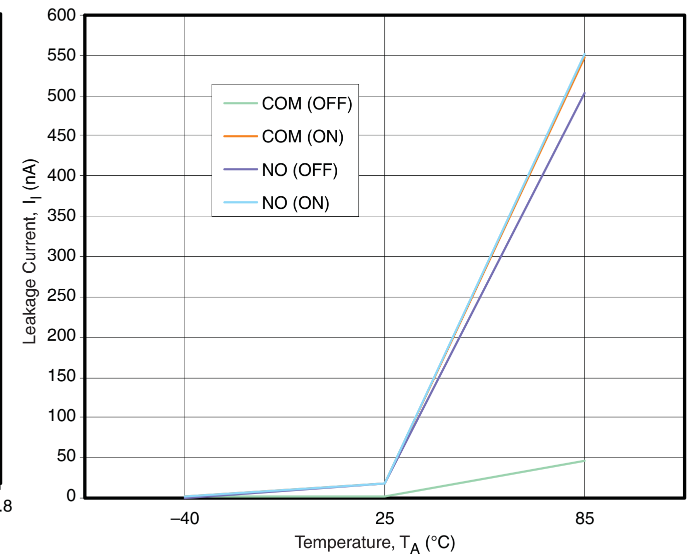


Figure 4. Leakage Current vs Temperature (V_+ = 3.3 V)

TYPICAL CHARACTERISTICS (continued)

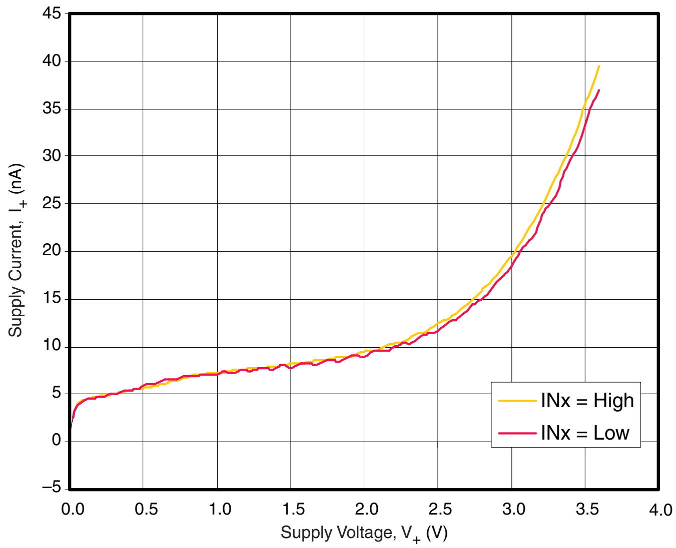


Figure 5. Supply Current vs Supply Voltage

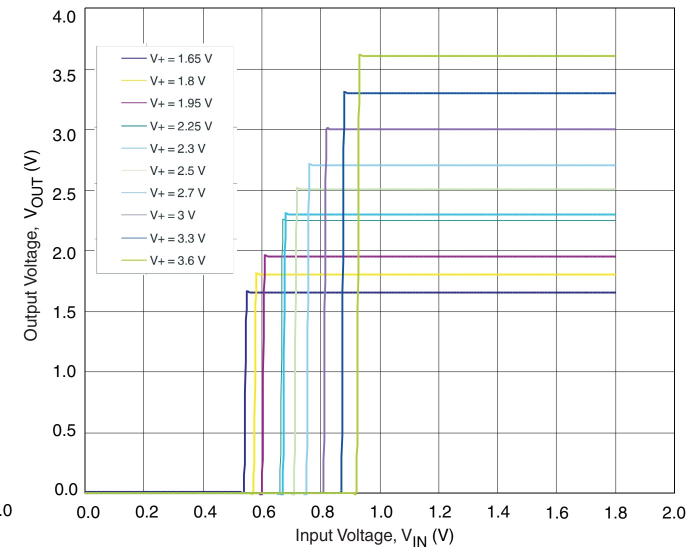


Figure 6. Control Input Thresholds (IN1, T_A = 25°C)

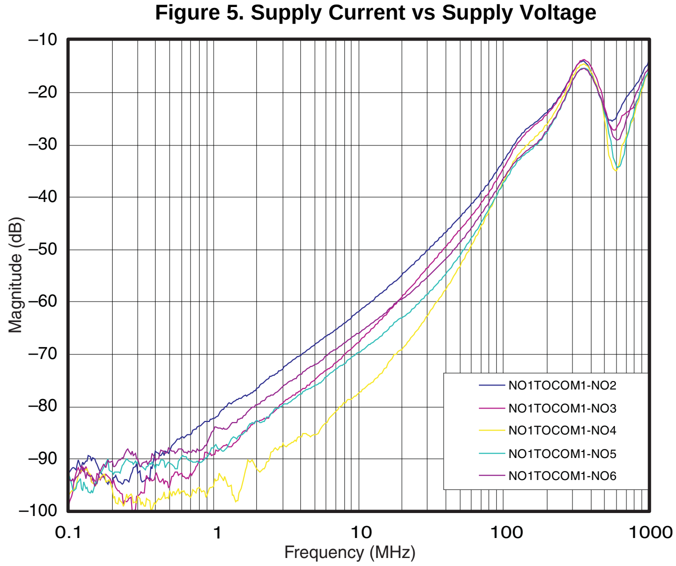


Figure 7. Crosstalk Adjacent

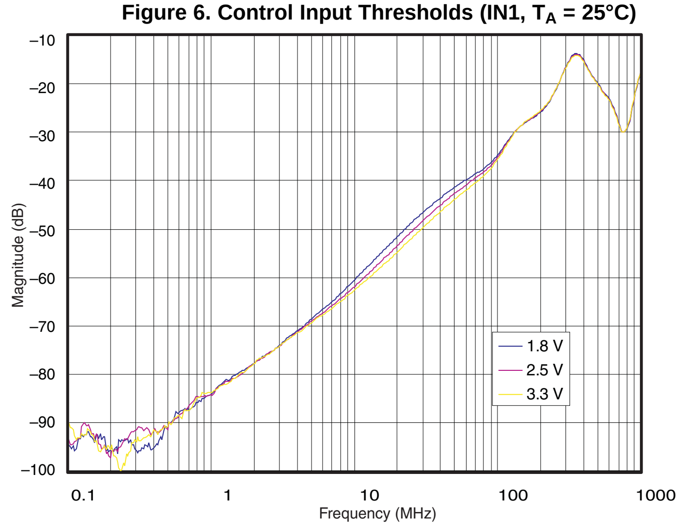


Figure 8. Crosstalk

TYPICAL CHARACTERISTICS (continued)

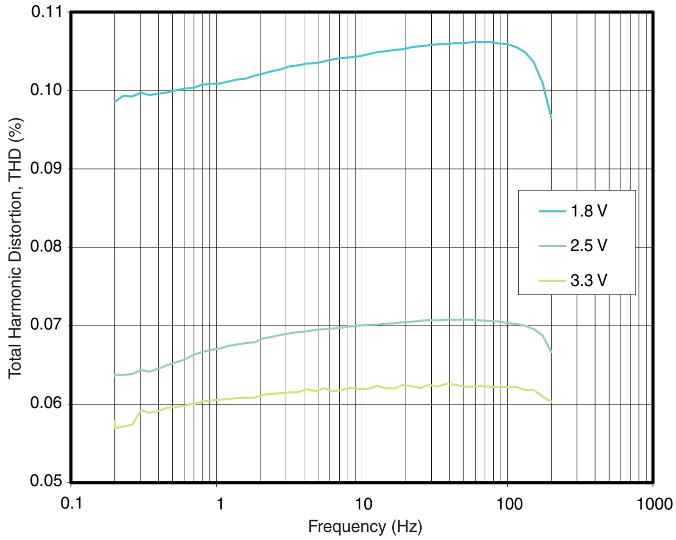


Figure 9. Total Harmonic Distortion vs Frequency

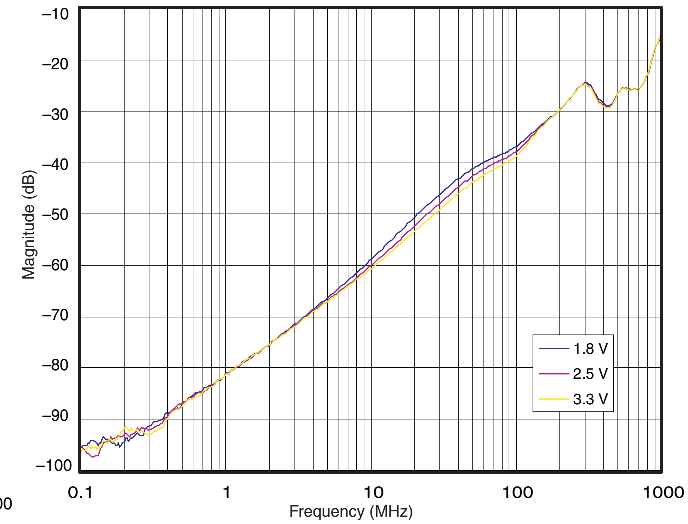


Figure 10. OFF Isolation

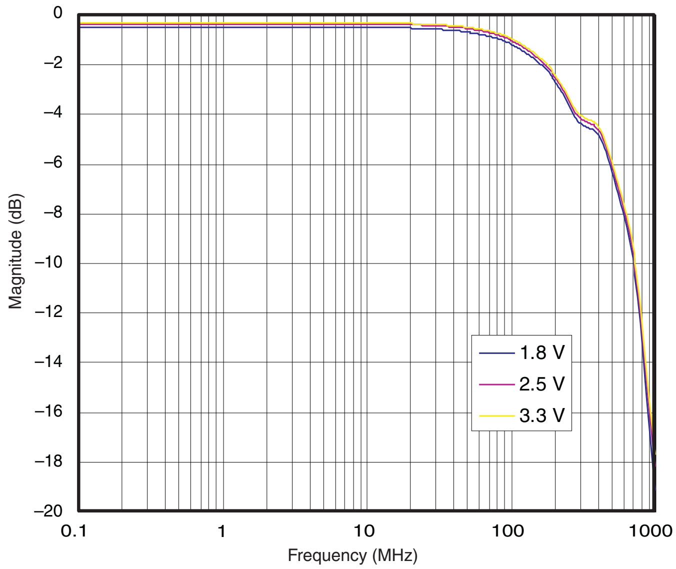


Figure 11. Insertion Loss

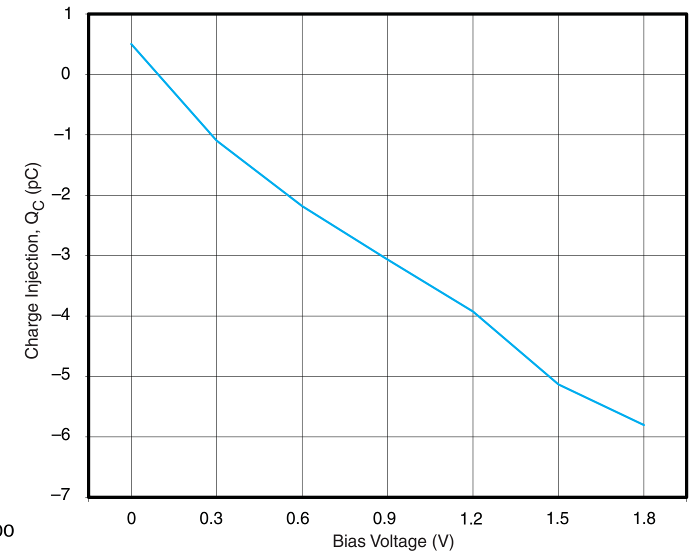


Figure 12. Charge Injection vs Bias Voltage (1.8 V)

TYPICAL CHARACTERISTICS (continued)

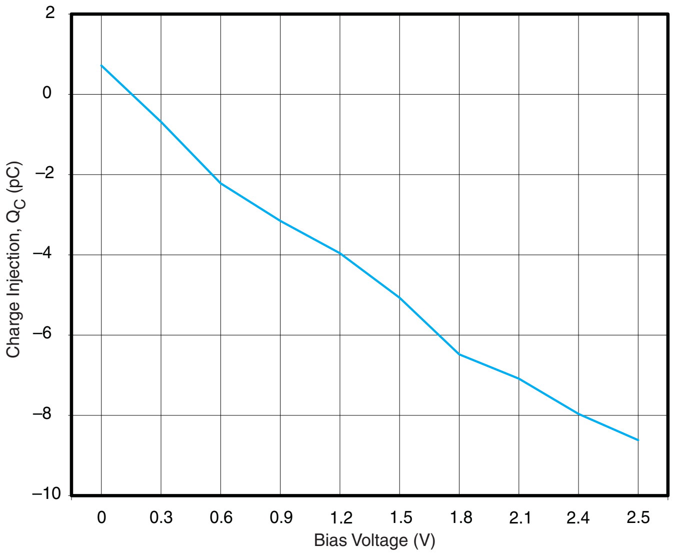


Figure 13. Charge Injection vs Bias Voltage (2.5 V)

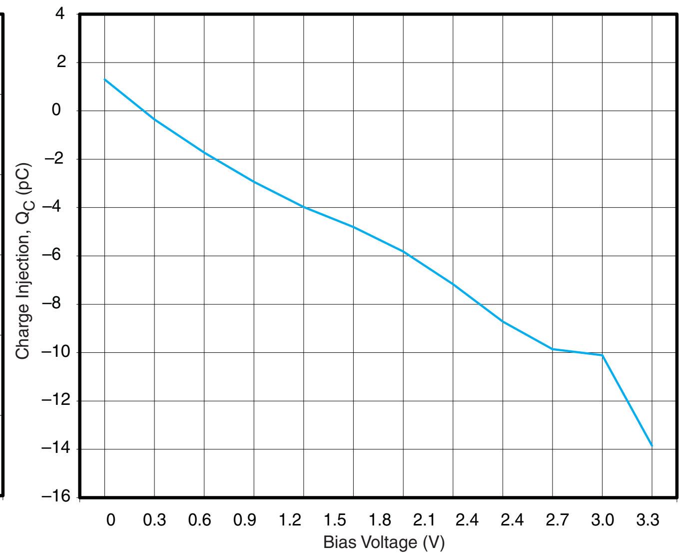


Figure 14. Charge Injection vs Bias Voltage (3.3 V)

PARAMETER MEASUREMENT INFORMATION

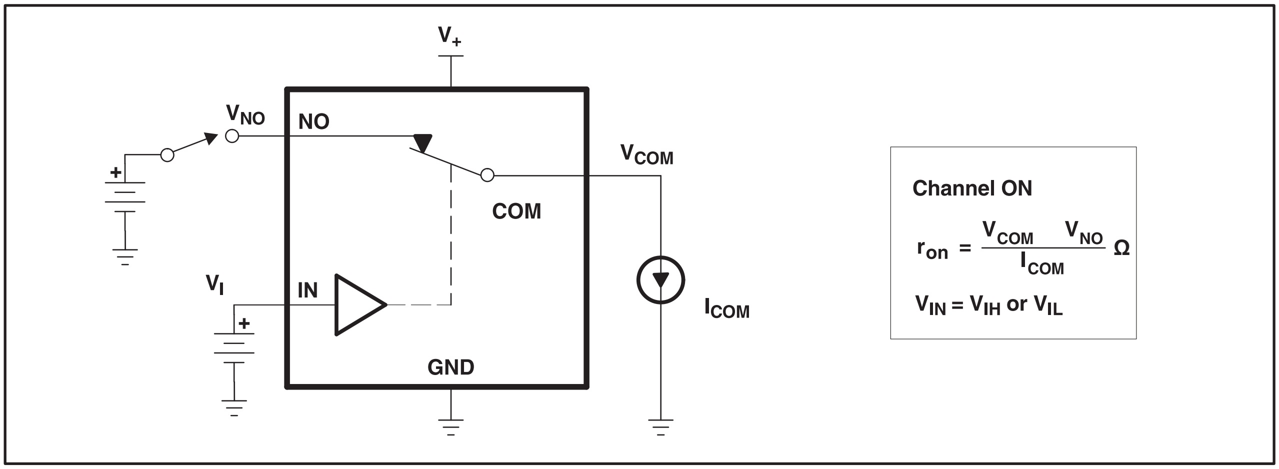


Figure 15. ON-state Resistance (r_{ON})

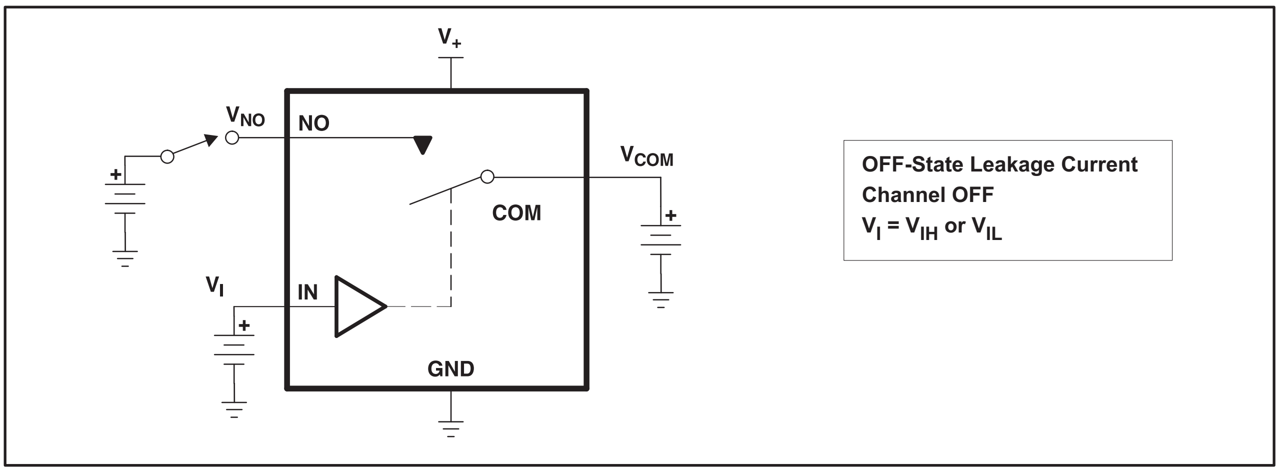


Figure 16. OFF-State Leakage Current
($I_{COM(OFF)}$, $I_{NC(OFF)}$, $I_{COM(PWROFF)}$, $I_{NC(PWROFF)}$)

PARAMETER MEASUREMENT INFORMATION (continued)

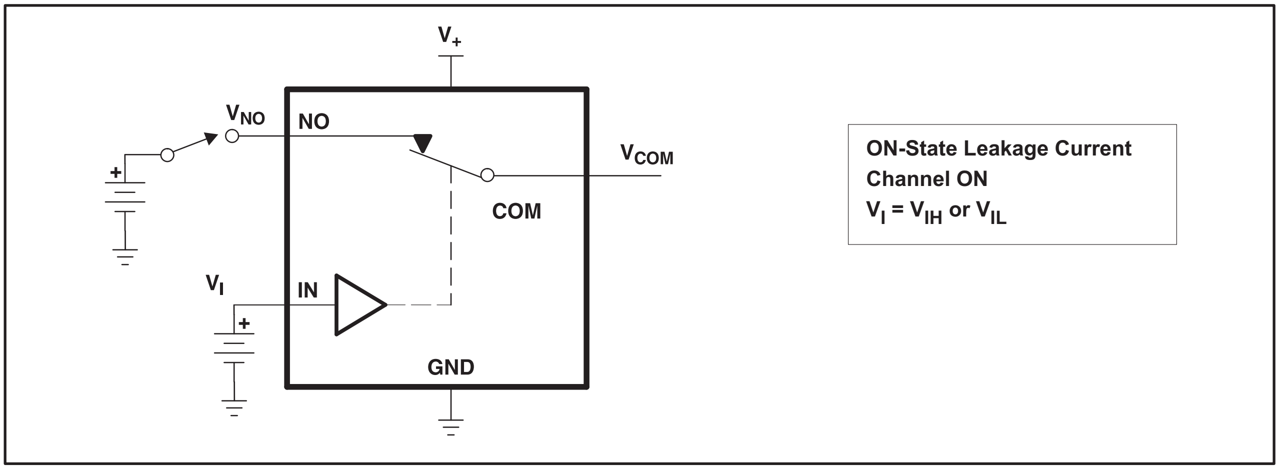


Figure 17. ON-State Leakage Current ($I_{COM(ON)}$, $I_{NC(ON)}$)

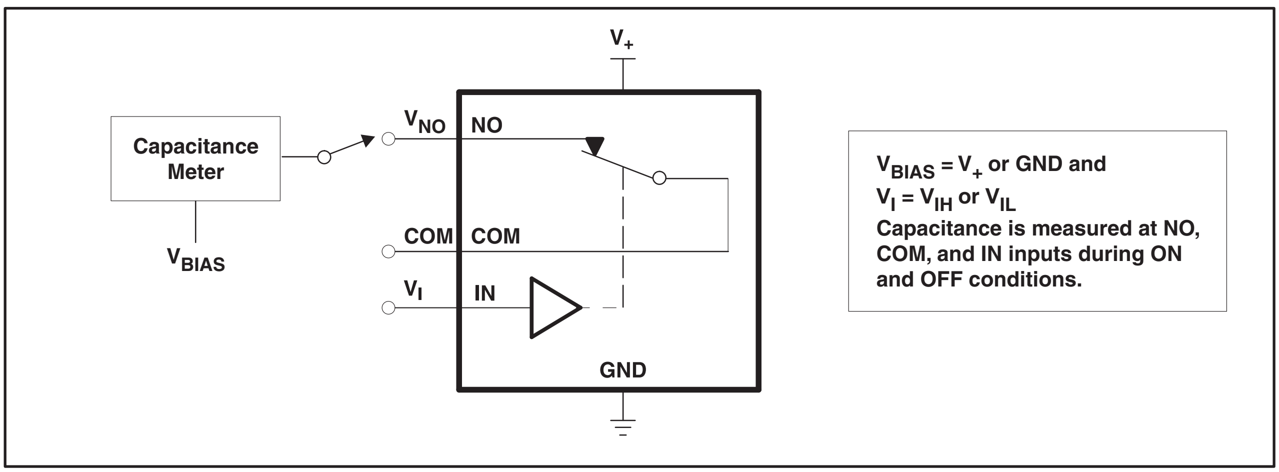
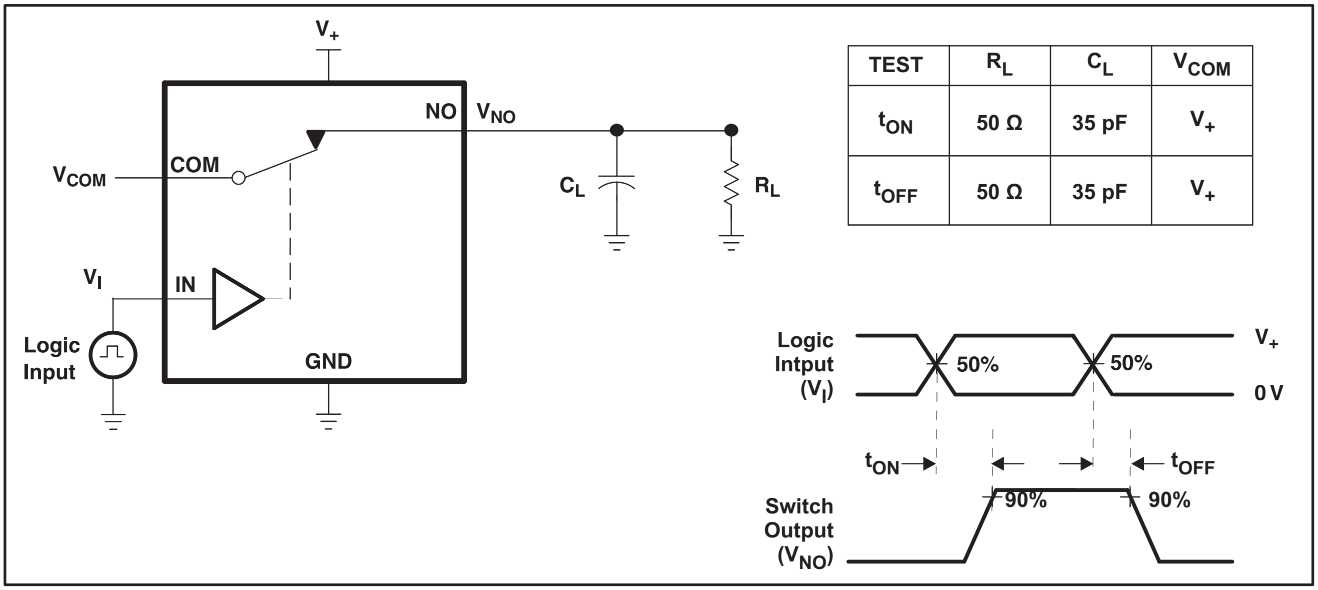


Figure 18. Capacitance (C_I, $C_{COM(OFF)}$, $C_{COM(ON)}$, $C_{NC(OFF)}$, $C_{NC(ON)}$)

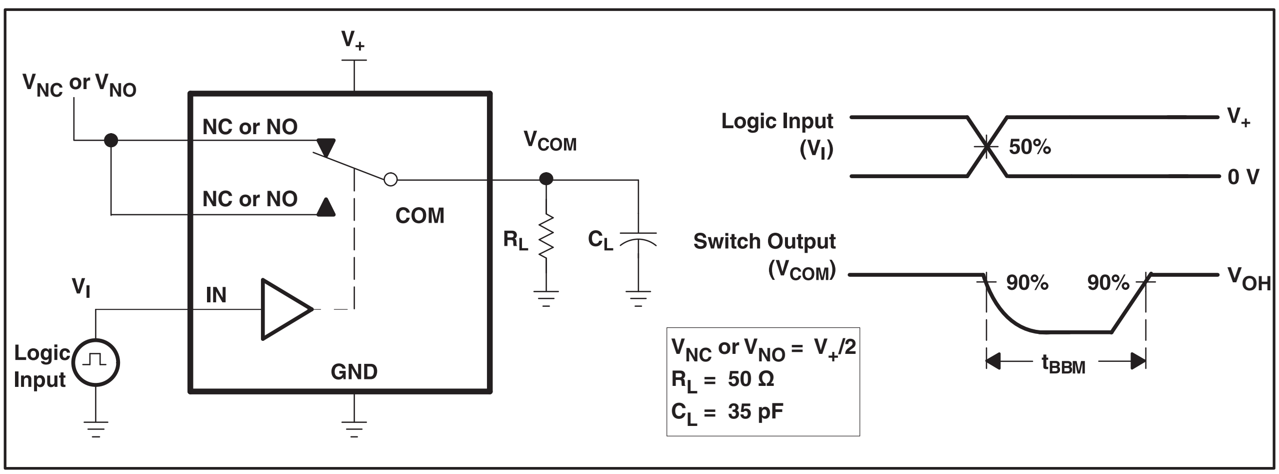
PARAMETER MEASUREMENT INFORMATION (continued)



A. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.

B. C_L includes probe and jig capacitance.

Figure 19. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})



A. C_L includes probe and jig capacitance.

B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.

Figure 20. Break-Before-Make Time (t_{BBM})

PARAMETER MEASUREMENT INFORMATION (continued)

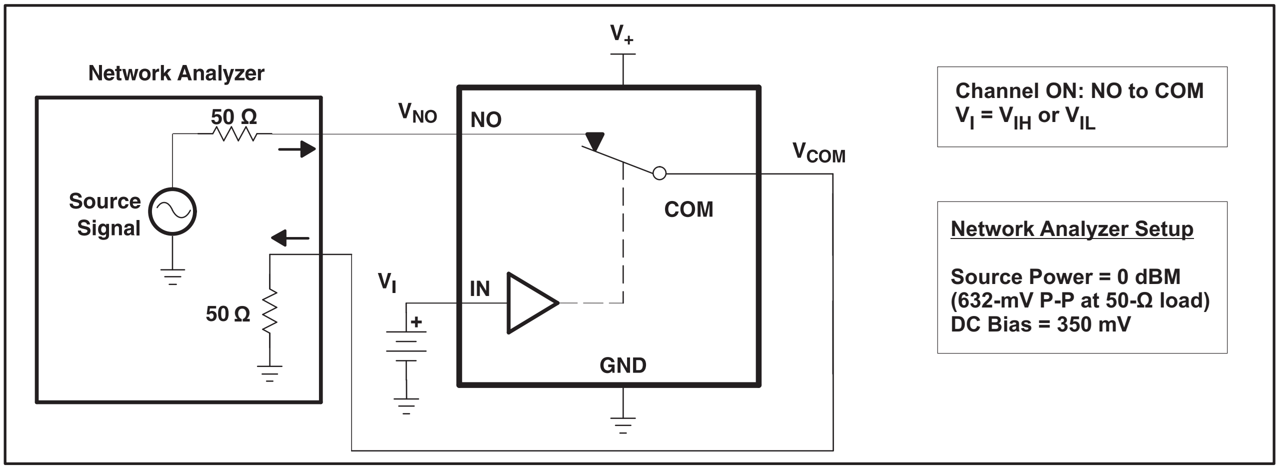


Figure 21. Bandwidth (BW)

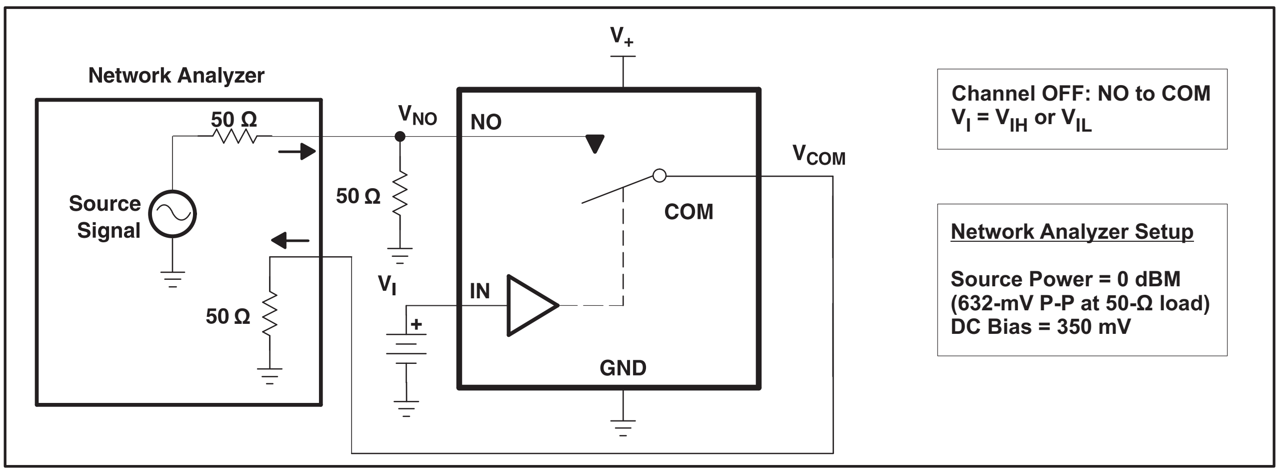


Figure 22. OFF Isolation (O_{ISO})

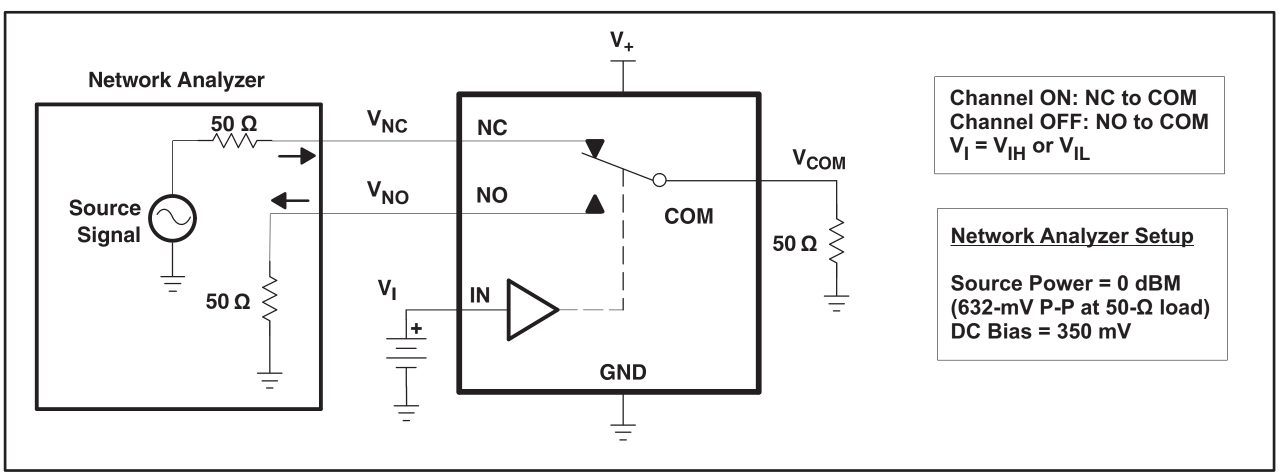
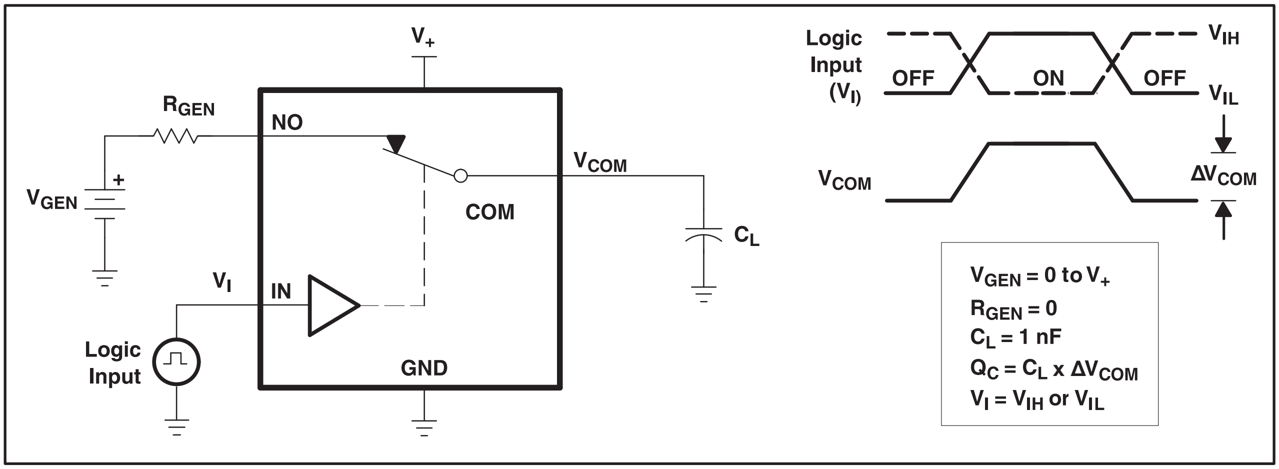


Figure 23. Crosstalk (X_{TALK})

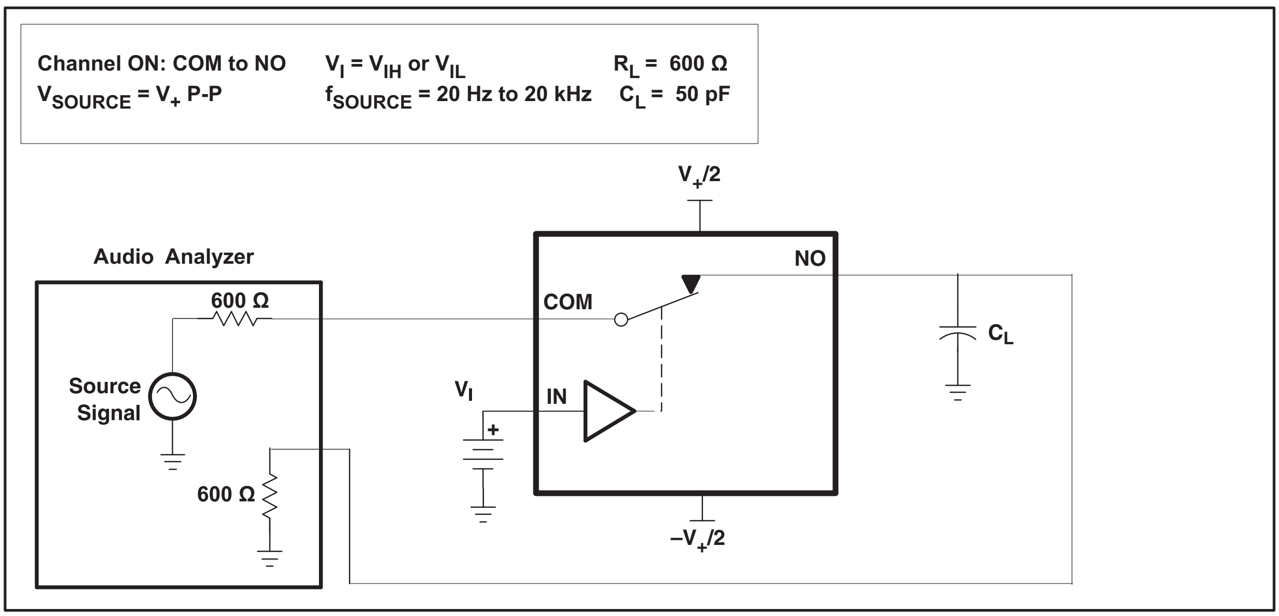
PARAMETER MEASUREMENT INFORMATION (continued)



A. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.

B. C_L includes probe and jig capacitance.

Figure 24. Charge Injection (Q_C)



A. C_L includes probe and jig capacitance.

Figure 25. Total Harmonic Distortion (THD)

PACKAGING INFORMATION

Orderable Device	Status [1]	Package Type	Package Drawing	Pins	Package Qty	Eco Plan [2]	Lead/Ball Finish	MSL Peak Temp [3]
TS3A27518EPWR	ACTIVE	TSSOP	PW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS3A27518ERTWR	ACTIVE	QFN	RTW	24	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TS3A27518EZQSR	ACTIVE	BGA MI CROSTA R JUNI OR	ZQS	24	2500	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM

[1] The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

[2] Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

[3] MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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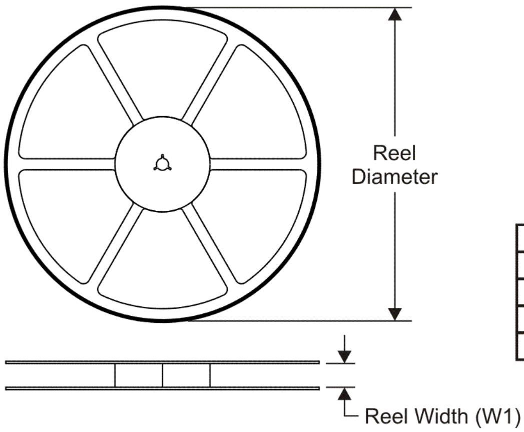
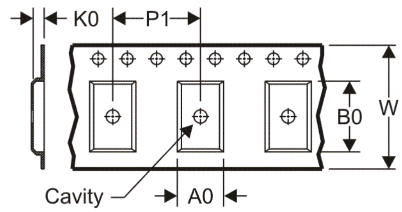
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

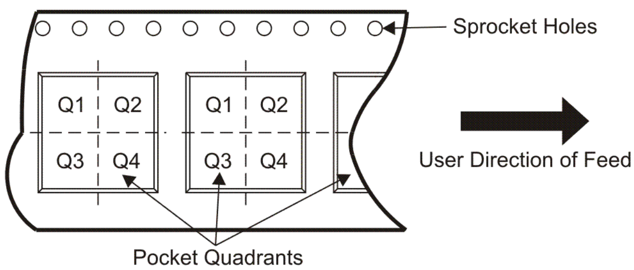


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

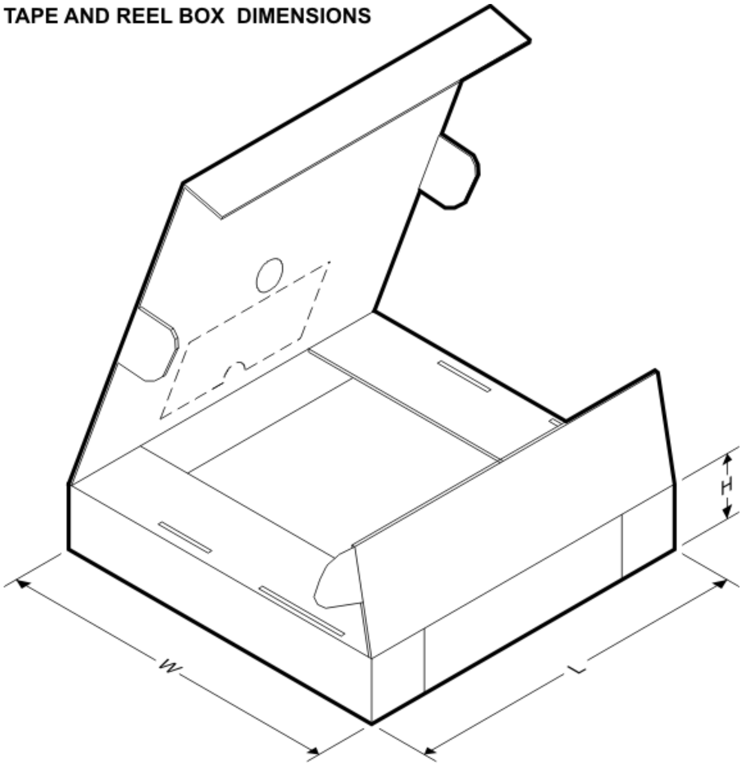
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS3A27518EPWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1
TS3A27518ERTWR	QFN	RTW	24	3000	330.0	12.4	4.3	4.3	1.5	8.0	12.0	Q2
TS3A27518EZQSR	BGA MI CROSTA R JUNI OR	ZQS	24	2500	330.0	12.4	3.3	3.3	1.6	8.0	12.0	Q1

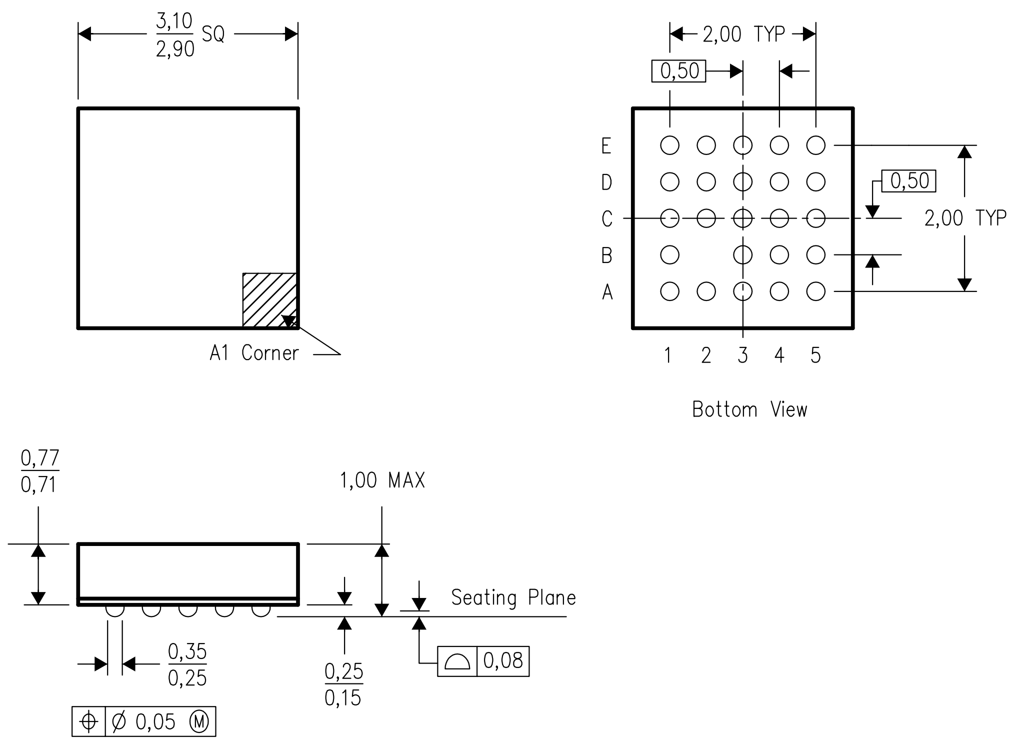
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS3A27518EPWR	TSSOP	PW	24	2000	346.0	346.0	33.0
TS3A27518ERTWR	QFN	RTW	24	3000	346.0	346.0	29.0
TS3A27518EZQSR	BGA MICROSTAR JUNIOR	ZQS	24	2500	340.5	338.1	20.6

ZQS (S–PBGA–N24) PLASTIC BALL GRID ARRAY

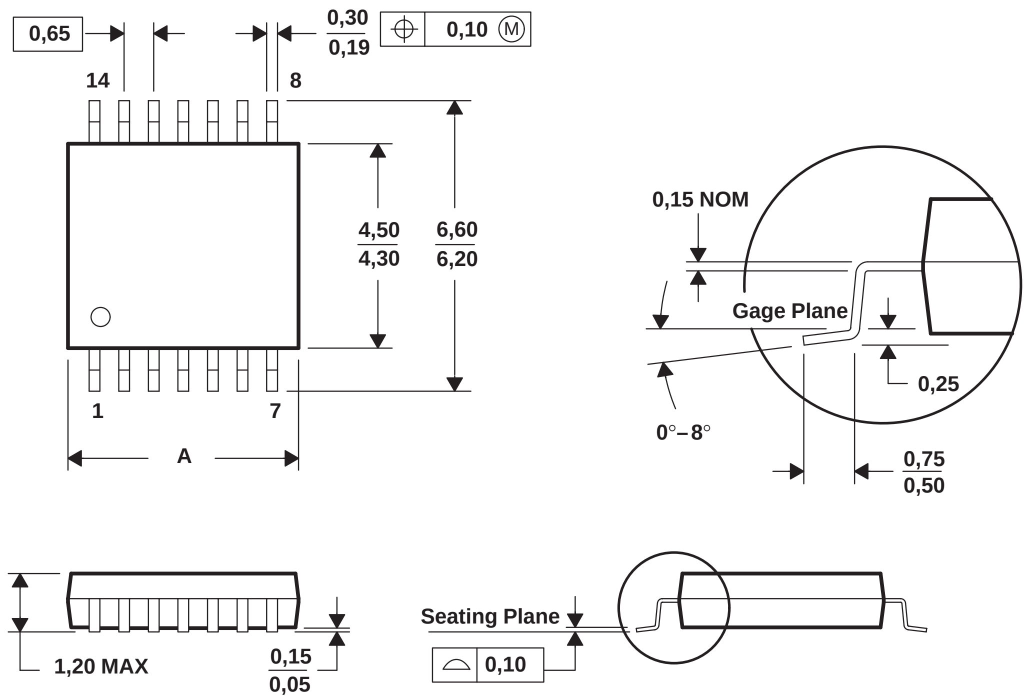


4206374/A 09/04

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Falls within JEDEC MO–225
D. This package is lead–free.

PW (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

14 PINS SHOWN

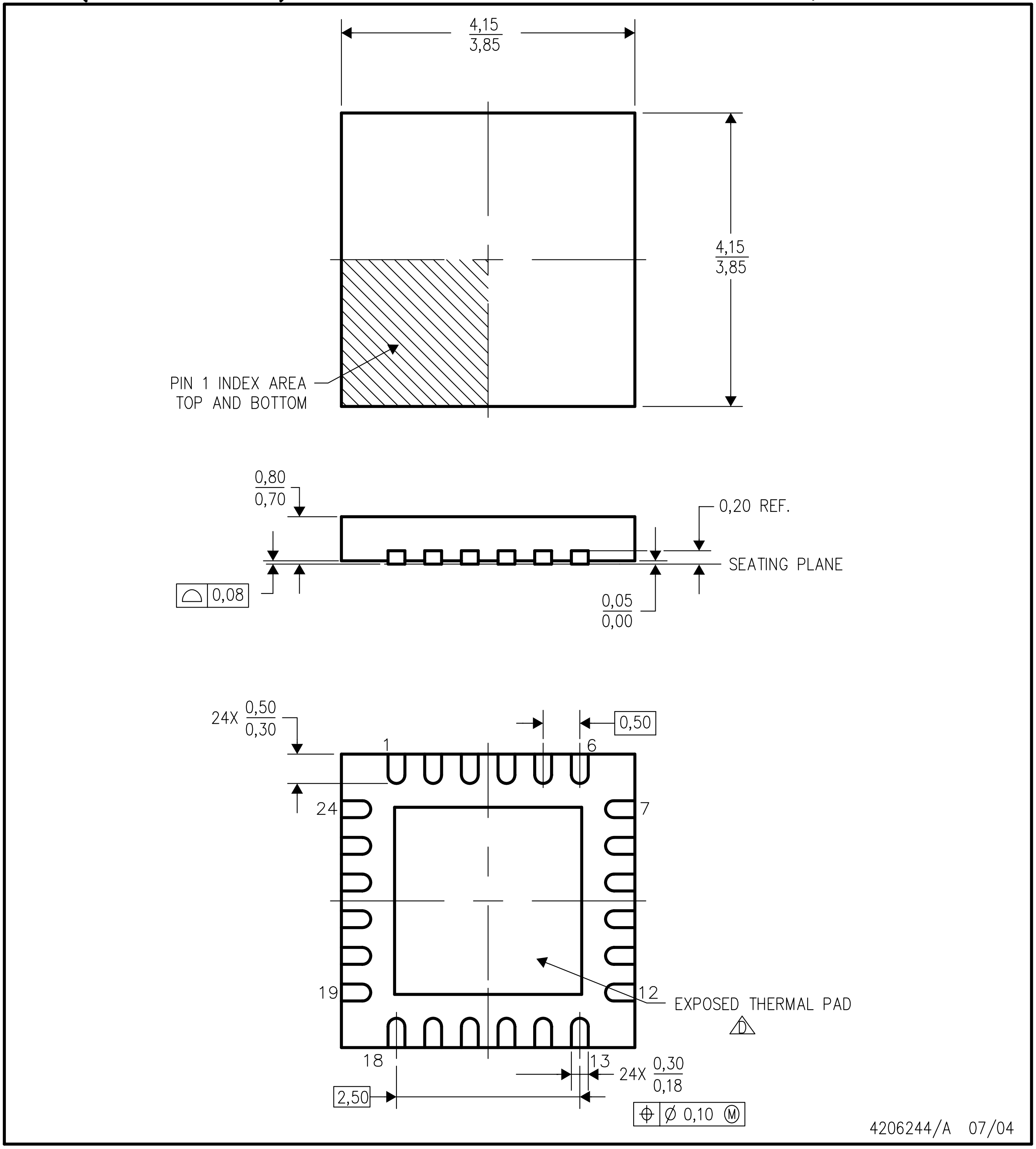


PINS ** / DIM	8	14	16	20	24	28
A MAX	3,10	5,10	5,10	6,60	7,90	9,80
A MIN	2,90	4,90	4,90	6,40	7,70	9,60

4040064/F 01/97

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
D. Falls within JEDEC MO-153

RTW (S-PQFP-N24) PLASTIC QUAD FLATPACK



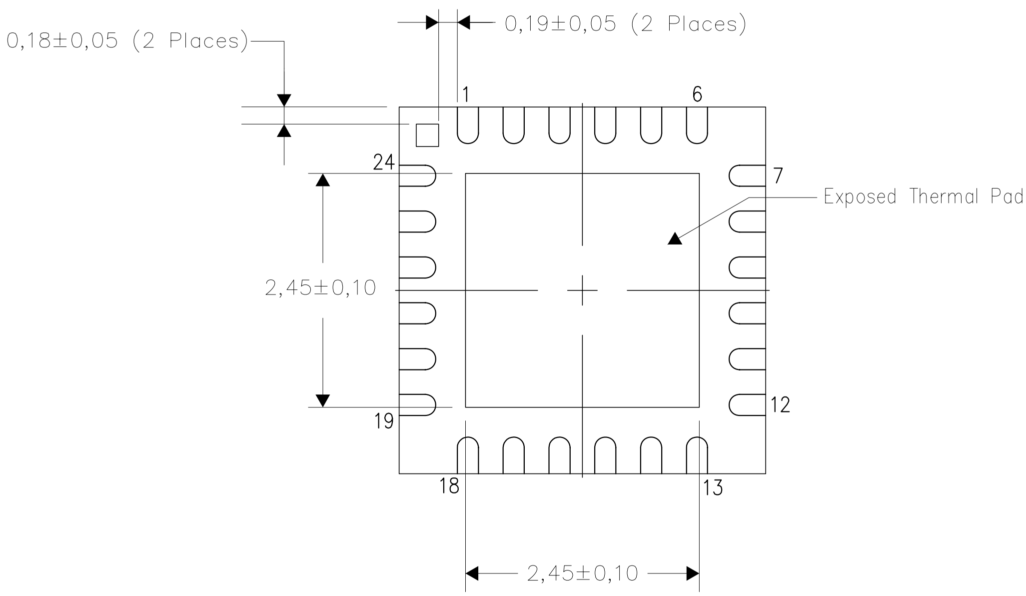
NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5–1994.
B. This drawing is subject to change without notice.
C. Quad Flatpack, No–Leads (QFN) package configuration.
D. The package thermal pad must be soldered to the board for thermal and mechanical performance. See the Product Data Sheet for details regarding the exposed thermal pad dimensions.
E. Falls within JEDEC MO–220.

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

NOTE: All linear dimensions are in millimeters

Exposed Thermal Pad Dimensions